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Upper critical field study of CH_4 HPCVD carbon-doped MgB_2
F. HUNTE, J. JAROSZYNSKI, A. GUREVICH, D.C. LARBALESTIER, NHMFL-Florida State University, Y. ZHU, P.M. VOYLES, University of Wisconsin, Madison, X.X. XI, K. CHEN, The Pennsylvania State University, S. BAILY, F. BALAKIREV, NHMFL-Los Alamos National Laboratory, C.G. ZHUANG, S. MENG , C. Y. ZHANG, Q.R. FENG, Z.Z. GAN, Peking University — The $H_{c2}(T)$ of a set of four carbon-doped MgB_2 films grown on both SiC and Al_2O_3substrates by HPCVD from methane CH_4 at flow rates from 7 to 10 sccm were measured in fields up to 65T. Compared to early metalorganic C sources which generated high $H_{c2}(0)$, these films have much lower resistivities and higher connectivities. The curvature of $H_{c2}(T)$ derived from low current four point magnetoresistance shows upturn at low temperatures, which is consistent with the dominance of π-band scattering in the theory of dirty two-gap superconductivity. $H_{c2}^{|}(0) > 60$T is close to the paramagnetic limit of ~ 66T for the 10 sccm film on SiC, though still a little lower than for the previously used metalorganic $(C_6H_7)_2Mg$. Differences in the $H_{c2}(T)$ behavior between films grown on the two substrates are attributed to variations in strain fields produced by the substrate coupled to the film at growth.

Frank Hunte
NHMFL-Florida State University

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